

Automotive P-Channel 12 V (D-S) 175 °C MOSFET

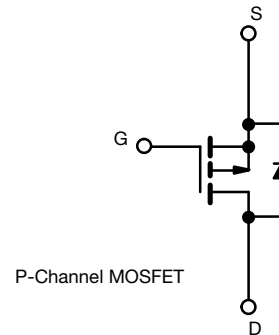
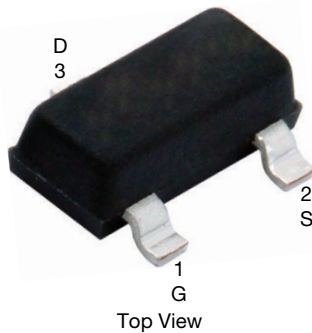
 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

| PRODUCT SUMMARY | |
|--|--------|
| V_{DS} (V) | -12 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V | 0.050 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = -2.5$ V | 0.068 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = -1.8$ V | 0.100 |
| I_D (A) | -5 |
| Configuration | Single |
| Package | SOT-23 |

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified ^c
- 100 % R_g and UIS tested
- Compliant to RoHS Directive 2002/95/EC
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912

SOT-23 (TO-236)

Marking Code: 8D

| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | |
|---|----------------|----------------|-------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | V_{DS} | -12 | V |
| Gate-Source Voltage | | V_{GS} | ± 8 | |
| Continuous Drain Current | $T_C = 25$ °C | I_D | -5 | A |
| | $T_C = 125$ °C | | -3 | |
| Continuous Source Current (Diode Conduction) | | I_S | -2.5 | |
| Pulsed Drain Current ^a | | I_{DM} | -20 | |
| Single Pulse Avalanche Current | L = 0.1 mH | I_{AS} | -11 | |
| Single Pulse Avalanche Energy | | E_{AS} | 6 | mJ |
| Maximum Power Dissipation ^a | $T_C = 25$ °C | P_D | 2 | W |
| | $T_C = 125$ °C | | 0.67 | |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +175 | °C |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|------------------------|------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-Ambient | PCB Mount ^b | R_{thJA} | 175 | °C/W |
| Junction-to-Foot (Drain) | | R_{thJF} | 75 | |

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.



| SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|--|--------------|---|--|-------|-------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | | -12 | - | - | V |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | | -0.45 | - | -1 | |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$ | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}$ | $V_{DS} = -12\text{ V}$ | - | - | -1 | μA |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -12\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | - | - | -50 | |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -12\text{ V}, T_J = 175\text{ }^\circ\text{C}$ | - | - | -150 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{GS} = -4.5\text{ V}$ | $V_{DS} \leq -5\text{ V}$ | -10 | - | - | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -4.5\text{ V}$ | $I_D = -3.5\text{ A}$ | - | 0.042 | 0.050 | Ω |
| | | $V_{GS} = -4.5\text{ V}$ | $I_D = -3.5\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | - | - | 0.066 | |
| | | $V_{GS} = -4.5\text{ V}$ | $I_D = -3.5\text{ A}, T_J = 175\text{ }^\circ\text{C}$ | - | - | 0.075 | |
| | | $V_{GS} = -2.5\text{ V}$ | $I_D = -3\text{ A}$ | - | 0.059 | 0.068 | |
| | | $V_{GS} = -1.8\text{ V}$ | $I_D = -2\text{ A}$ | - | 0.084 | 0.100 | |
| Forward Transconductance ^b | g_{fs} | $V_{DS} = -5\text{ V}, I_D = -1.6\text{ A}$ | | - | 7 | - | S |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}$ | $V_{DS} = -6\text{ V}, f = 1\text{ MHz}$ | - | 695 | 870 | μF |
| Output Capacitance | C_{oss} | | | - | 265 | 335 | |
| Reverse Transfer Capacitance | C_{rss} | | | - | 190 | 240 | |
| Total Gate Charge ^c | Q_g | $V_{GS} = -4.5\text{ V}$ | $V_{DS} = -6\text{ V}, I_D = -3.85\text{ A}$ | - | 9 | 13 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | - | 1 | - | |
| Gate-Drain Charge ^c | Q_{gd} | | | - | 2.4 | - | |
| Gate Resistance | R_g | f = 1 MHz | | 2.4 | 4.9 | 12.3 | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = -6\text{ V}, R_L = 1.6\text{ }\Omega$ $I_D \cong -3.85\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$ | - | 17 | 26 | ns | |
| Rise Time ^c | t_r | | - | 19 | 29 | | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | - | 28 | 42 | | |
| Fall Time ^c | t_f | | - | 13 | 20 | | |
| Source-Drain Diode Ratings and Characteristics ^b | | | | | | | |
| Pulsed Current ^a | I_{SM} | | | - | - | -20 | A |
| Forward Voltage | V_{SD} | $I_F = -2\text{ A}, V_{GS} = 0\text{ V}$ | | - | -0.8 | -1.2 | V |

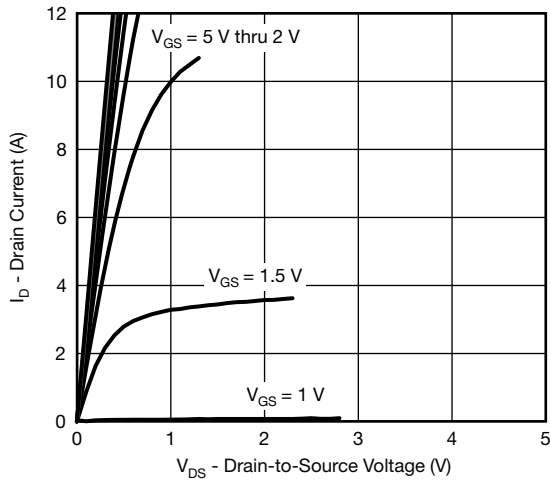
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

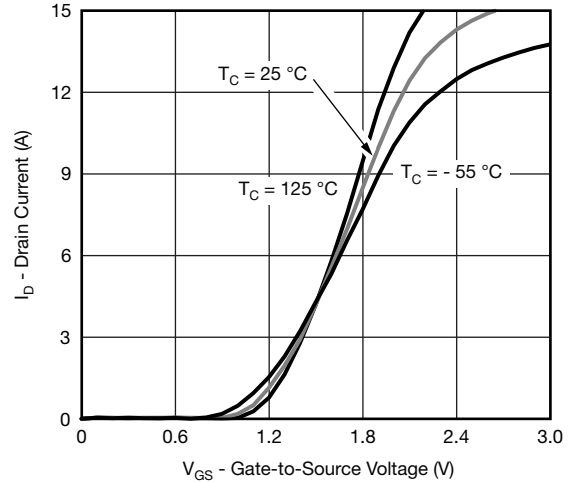
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



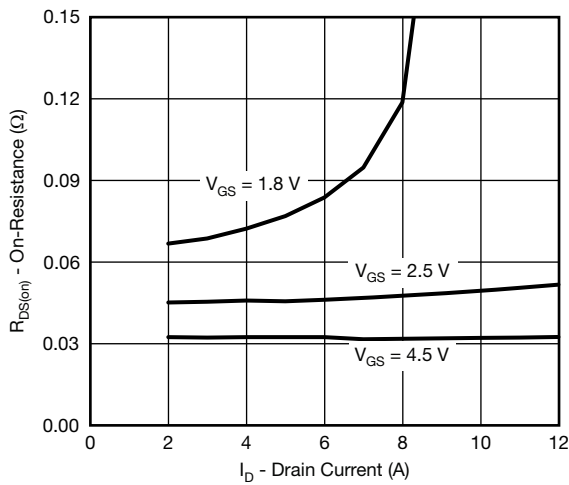
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



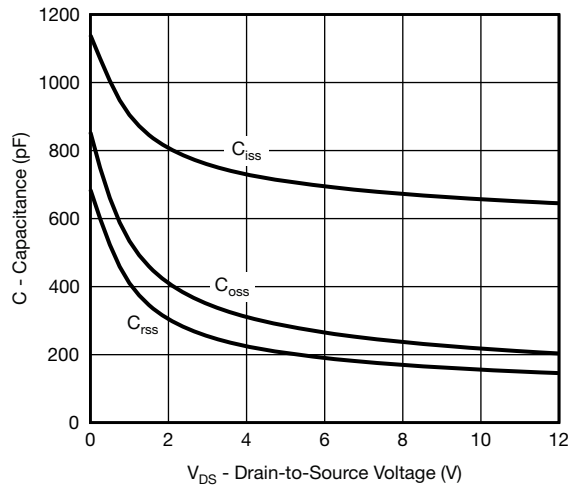
Output Characteristics



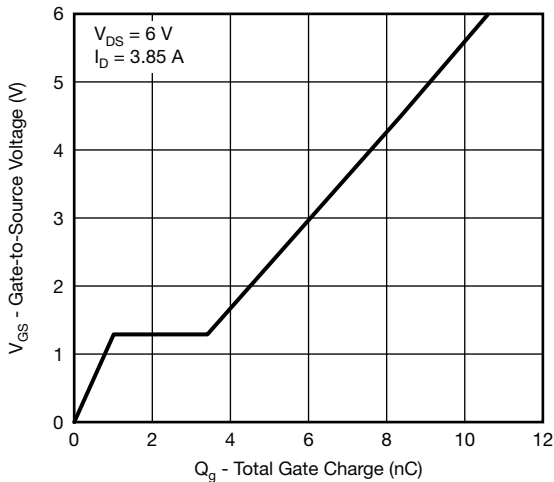
Transfer Characteristics



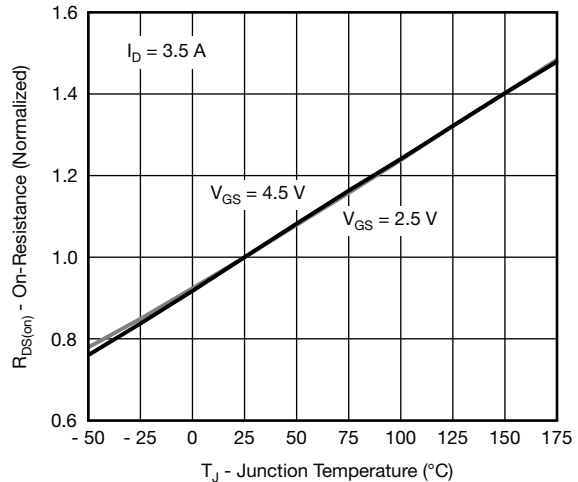
On-Resistance vs. Drain Current



Capacitance



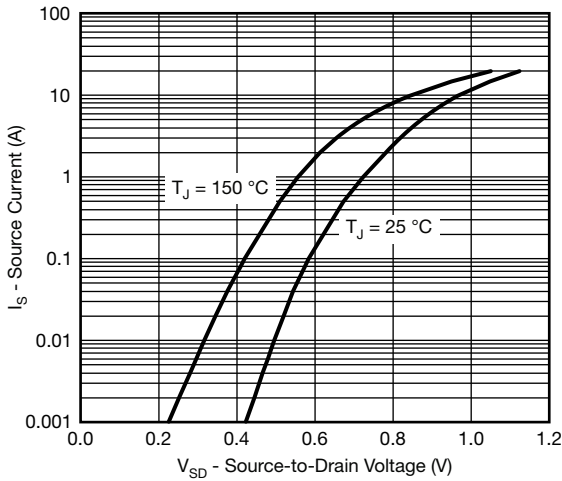
Gate Charge



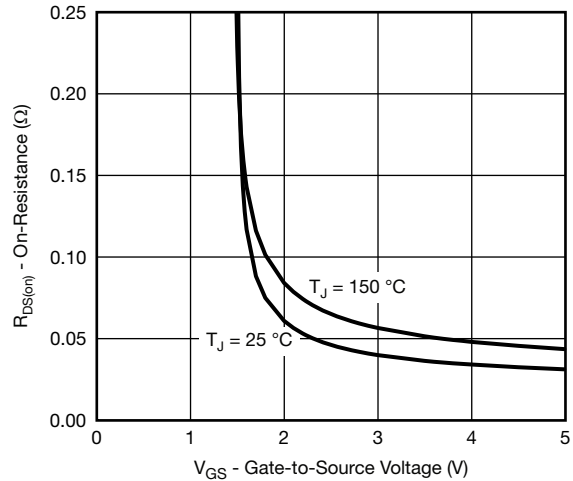
On-Resistance vs. Junction Temperature



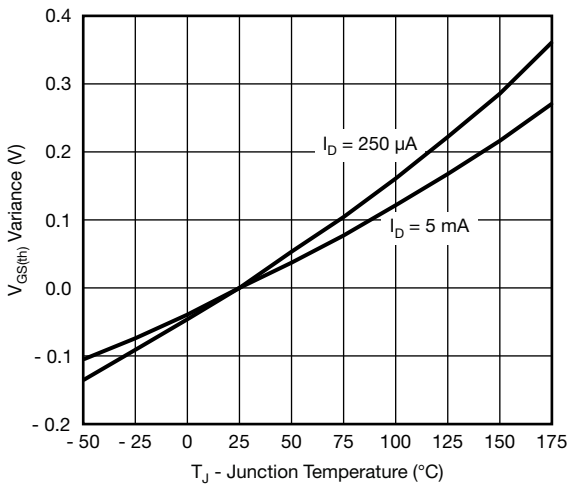
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



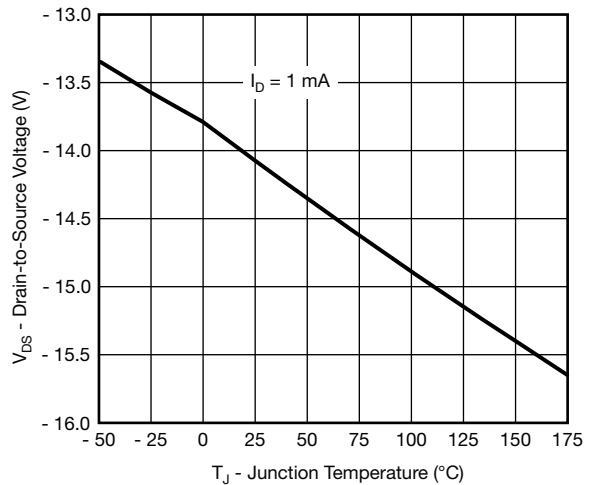
Source-Drain Diode Forward Voltage



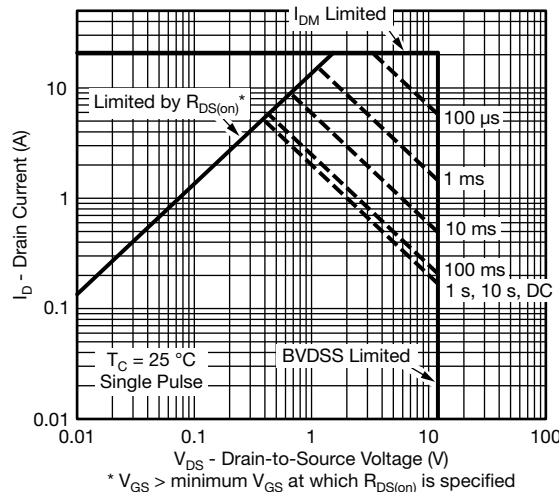
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



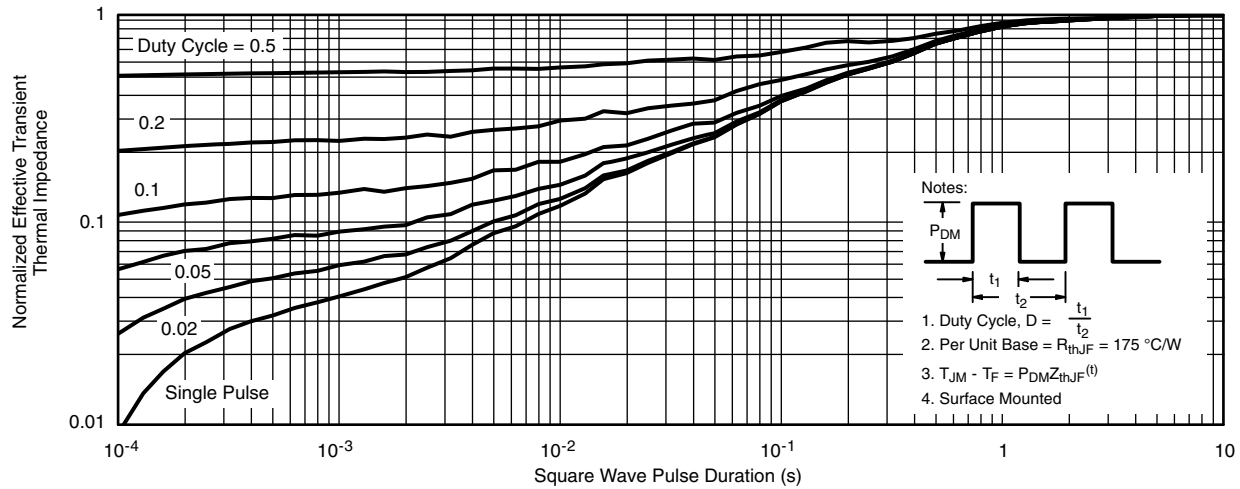
Drain Source Breakdown vs. Junction Temperature



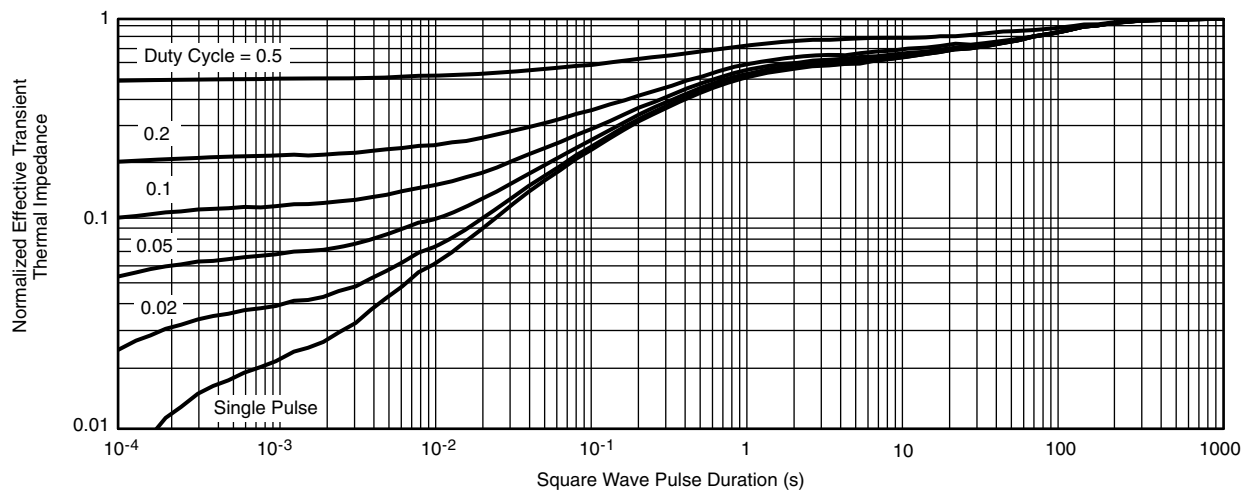
Safe Operating Area



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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| REVISION HISTORY ^a | | |
|--------------------------------------|-------------|----------------------------------|
| REVISION | DATE | DESCRIPTION OF CHANGE |
| D | 06-Oct-15 | • $R_{DS(on)}$ and R_g changed |

Note

a. As of April 2014

SOT-23 (TO-236): 3-LEAD



| Dim | MILLIMETERS | | INCHES | |
|----------------|-------------|------|------------|-------|
| | Min | Max | Min | Max |
| A | 0.89 | 1.12 | 0.035 | 0.044 |
| A ₁ | 0.01 | 0.10 | 0.0004 | 0.004 |
| A ₂ | 0.88 | 1.02 | 0.0346 | 0.040 |
| b | 0.35 | 0.50 | 0.014 | 0.020 |
| c | 0.085 | 0.18 | 0.003 | 0.007 |
| D | 2.80 | 3.04 | 0.110 | 0.120 |
| E | 2.10 | 2.64 | 0.083 | 0.104 |
| E ₁ | 1.20 | 1.40 | 0.047 | 0.055 |
| e | 0.95 BSC | | 0.0374 Ref | |
| e ₁ | 1.90 BSC | | 0.0748 Ref | |
| L | 0.40 | 0.60 | 0.016 | 0.024 |
| L ₁ | 0.64 Ref | | 0.025 Ref | |
| S | 0.50 Ref | | 0.020 Ref | |
| q | 3° | 8° | 3° | 8° |

ECN: S-03946-Rev. K, 09-Jul-01
 DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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